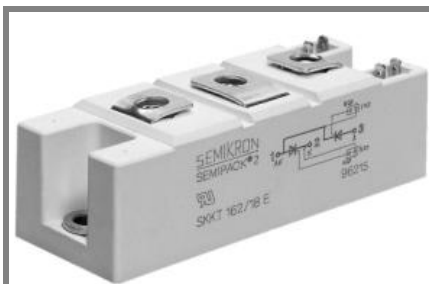


SKKT 162, SKKH 162



SEMIPACK® 2

Thyristor / Diode Modules

SKKT 162

SKKH 162

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

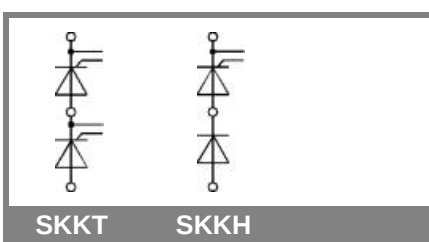
Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 250$ A (maximum value for continuous operation) $I_{TAV} = 160$ A (sin. 180; $T_c = 83$ °C)		
900	800	SKKT 162/08E	SKKH 162/08E	
1300	1200	SKKT 162/12E	SKKH 162/12E	
1500	1400	SKKT 162/14E	SKKH 162/14E	
1700	1600	SKKT 162/16E	SKKH 162/16E	
1900	1800	SKKT 162/18E	SKKH 162/18E	

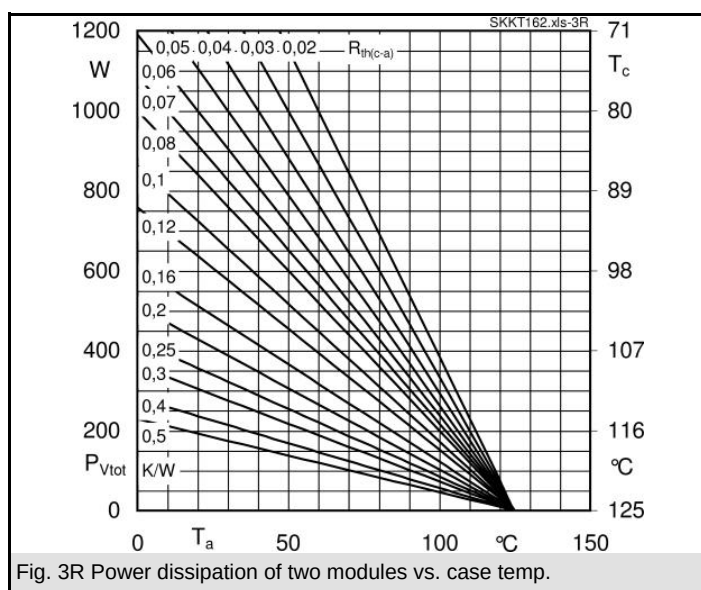
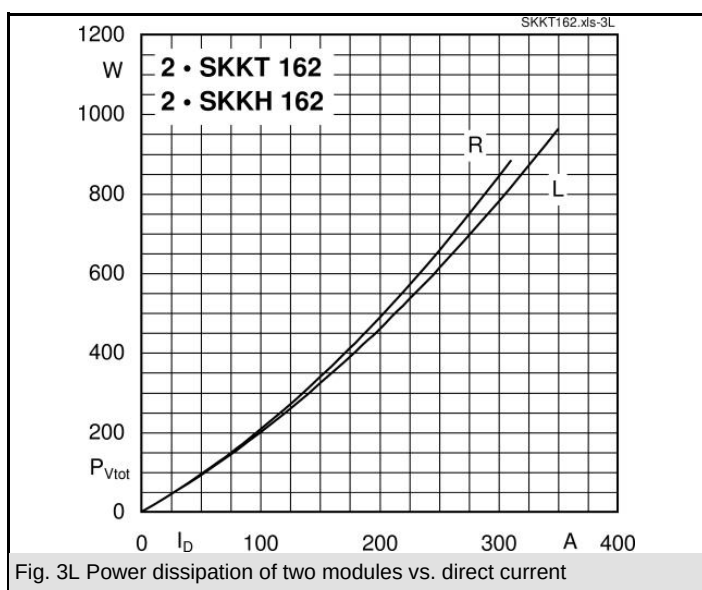
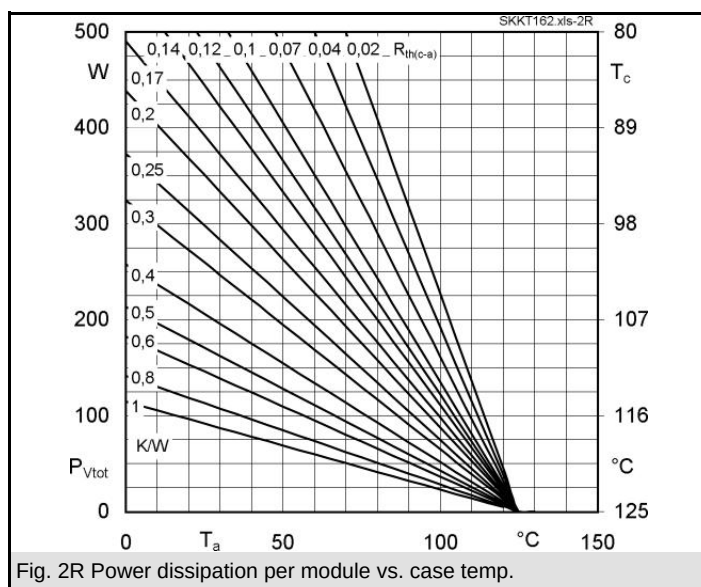
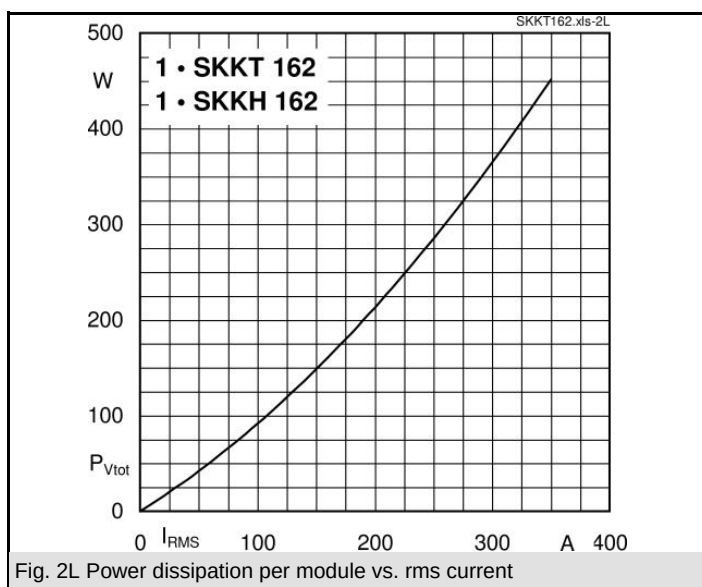
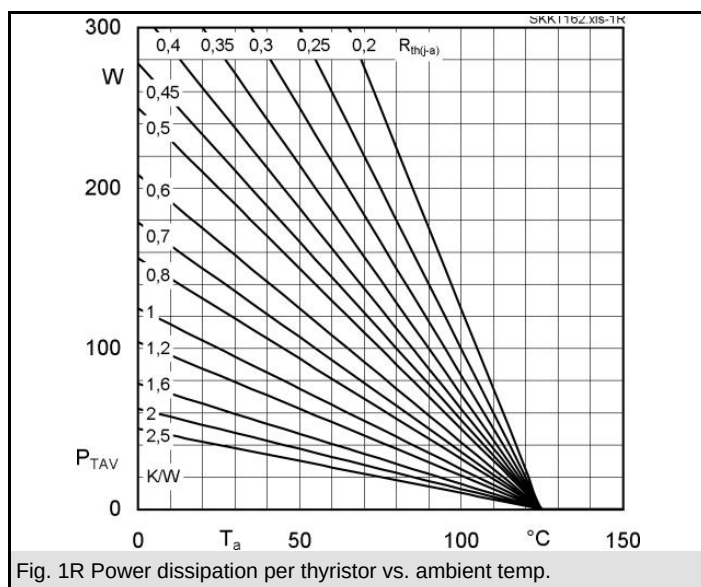
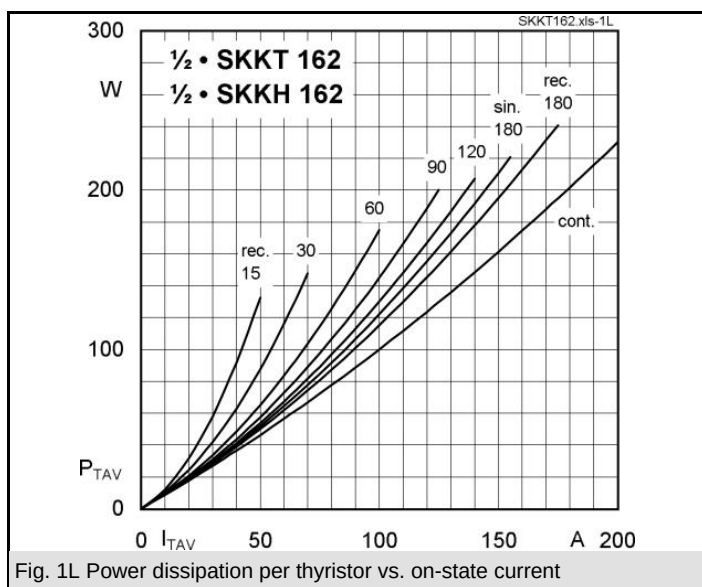
Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C	156 (110)	A
I_D	P3/180F; $T_a = 35$ °C; B2 / B6	190 / 230	A
I_{RMS}	P3/180F; $T_a = 35$ °C; W1 / W3	265 / 3 * 185	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	5400	A
	$T_{vj} = 125$ °C; 10 ms	5000	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	145000	A²s
	$T_{vj} = 125$ °C; 8,3 ... 10 ms	125000	A²s
V_T	$T_{vj} = 25$ °C; $I_T = 500$ A	max. 1,6	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,85	V
r_T	$T_{vj} = 125$ °C	max. 1,5	mΩ
I_{DD}, I_{RD}	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}, V_{DD} = V_{DRM}$	max. 40	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 200	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
t_q	$T_{vj} = 125$ °C	50 ... 150	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 400	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 1000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,17 / 0,085	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,18 / 0,09	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,2 / 0,1	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminal	5 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	165	g
Case	SKKT	A 21	
	SKKH	A 22	



SKKT

SKKH

SKKT 162, SKKH 162



SKKT 162, SKKH 162

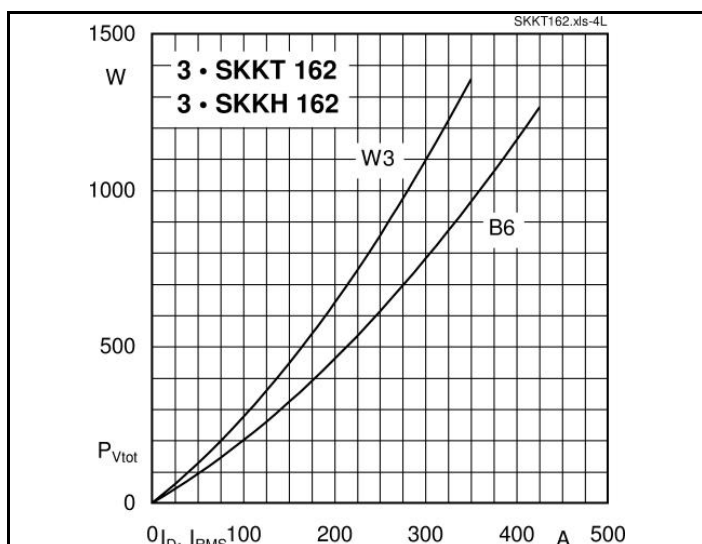


Fig. 4L Power dissipation of three modules vs. direct and rms current

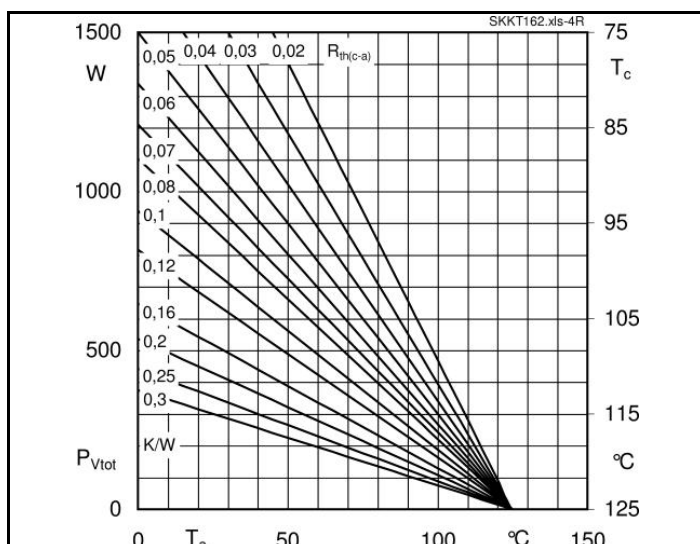


Fig. 4R Power dissipation of three modules vs. case temp.

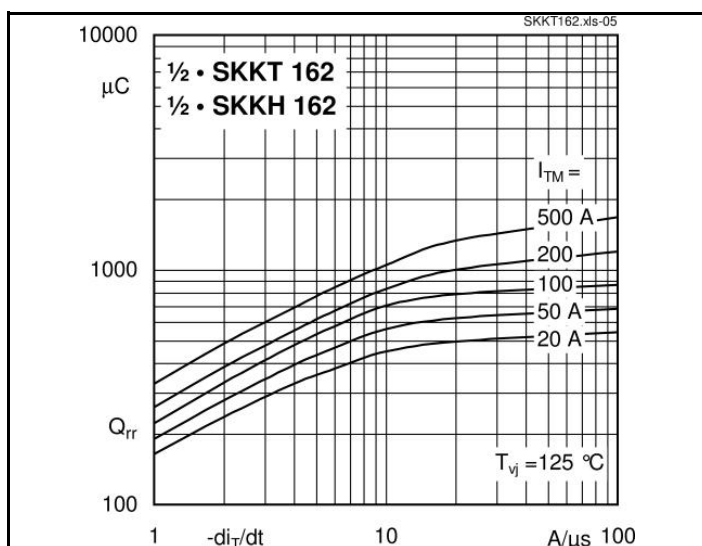


Fig. 5 Recovered charge vs. current decrease

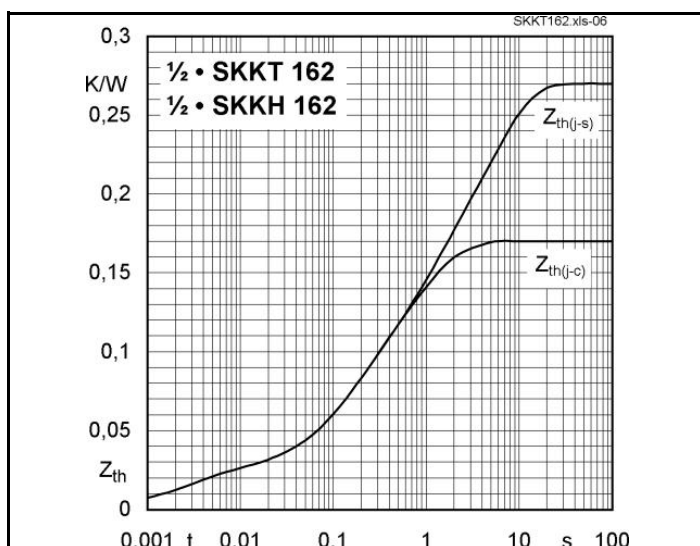


Fig. 6 Transient thermal impedance vs. time

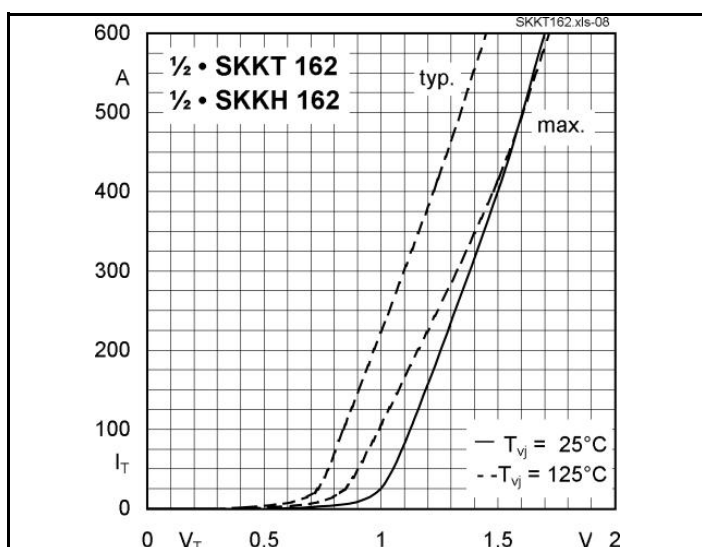


Fig. 7 On-state characteristics

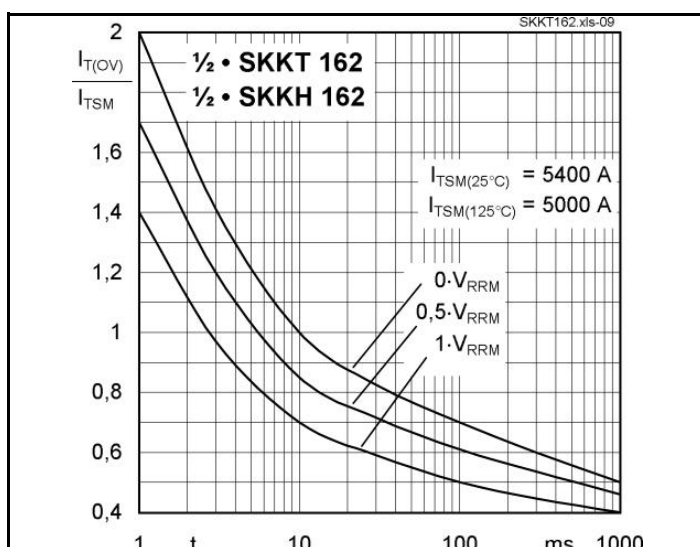
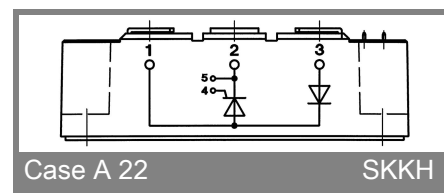
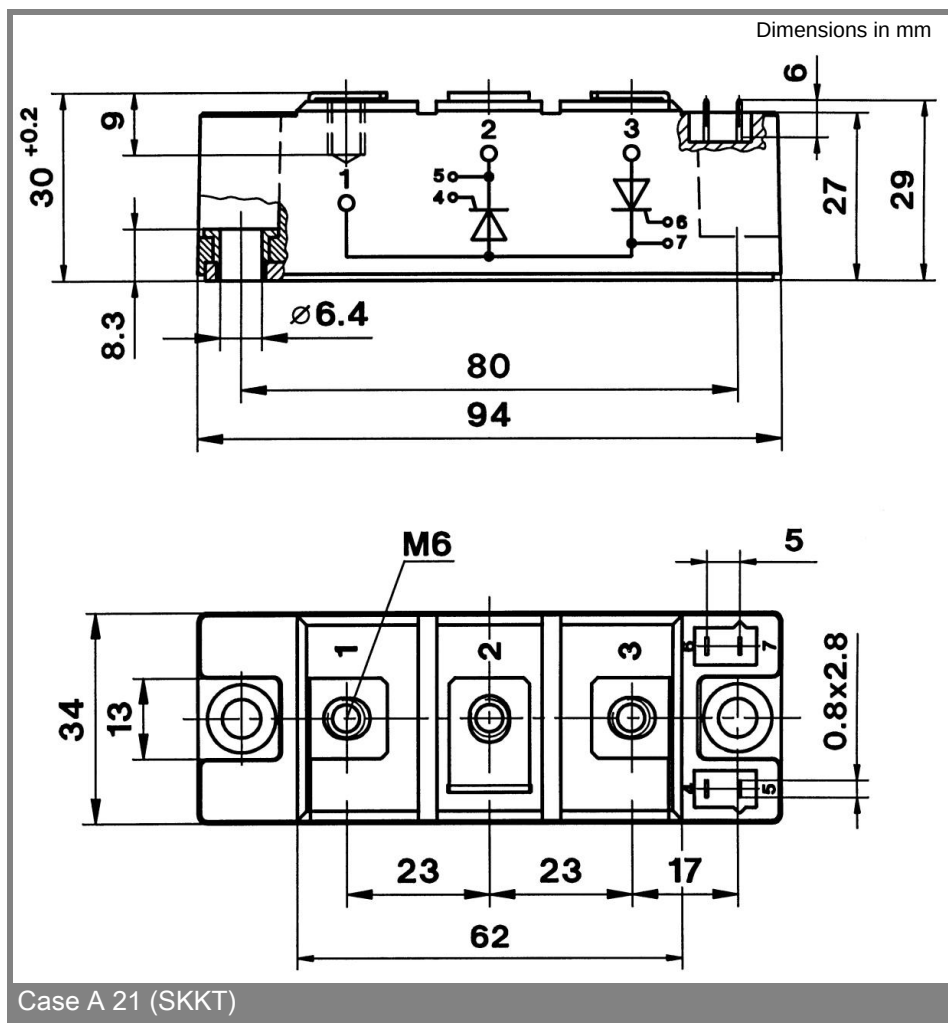
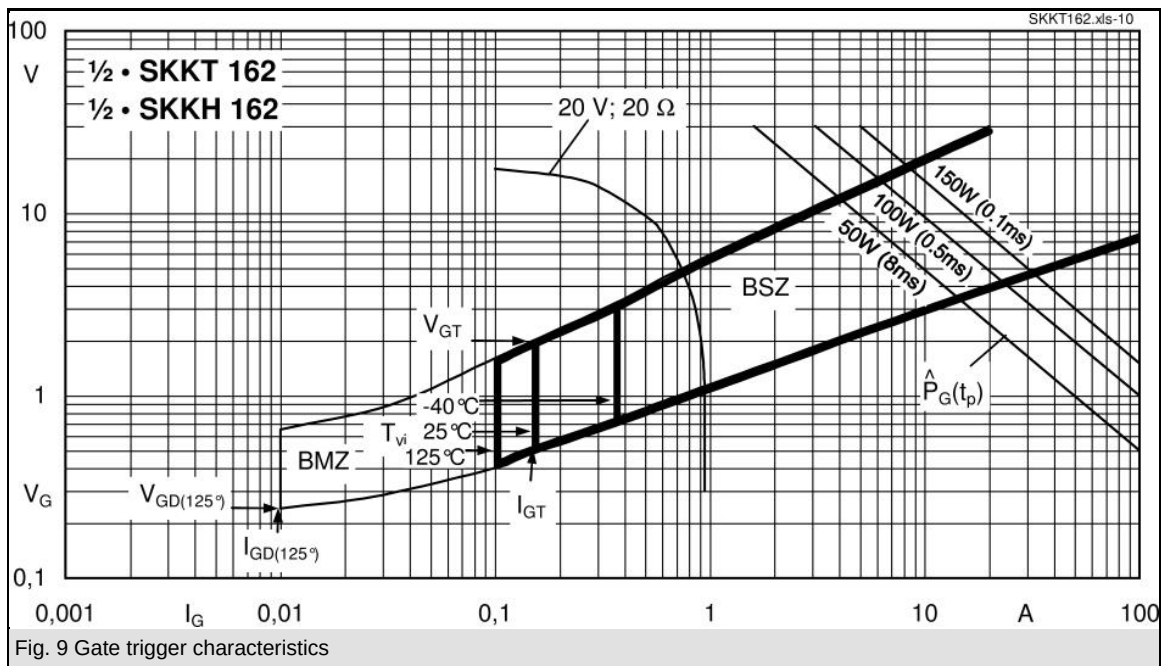


Fig. 8 Surge overload current vs. time

SKKT 162, SKKH 162



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